

HRW36

Silicon Schottky Barrier Diode for High Frequency Rectifying

HITACHI

Rev. 2
Nov. 1994

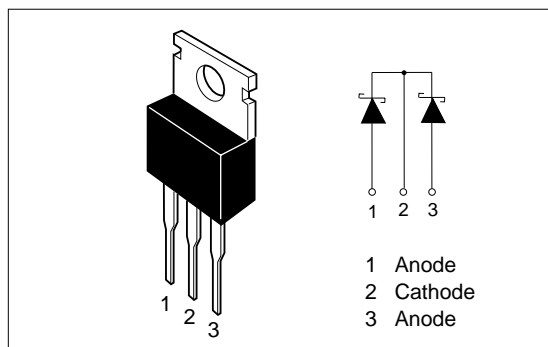
Features

- Low forward voltage drop. ($V_F = 0.80V$ max)
- High reverse voltage. ($V_R = 90V$ max)

Ordering Information

| Type No. | Laser Mark | Package Code |
|----------|------------|--------------|
| HRW36 | HRW36 | TO-220AB |

Pin Arrangement



Absolute Maximum Ratings ($T_a = 25^\circ C$) *

| Item | Symbol | Value | Unit |
|---|-----------------|-------------|------------|
| Repetitive peak reverse voltage | V_{RRM} | 90 | V |
| Average forward current | I_o^{**} | 10 | A |
| Non-Repetitive peak forward surge current | I_{FSM}^{***} | 70 | A |
| Junction temperature | T_j | 125 | $^\circ C$ |
| Storage temperature | T_{stg} | -40 to +125 | $^\circ C$ |

* Per one device

** Square wave, Duty (1/2), $T_c = 95^\circ C$, Sum of two devices

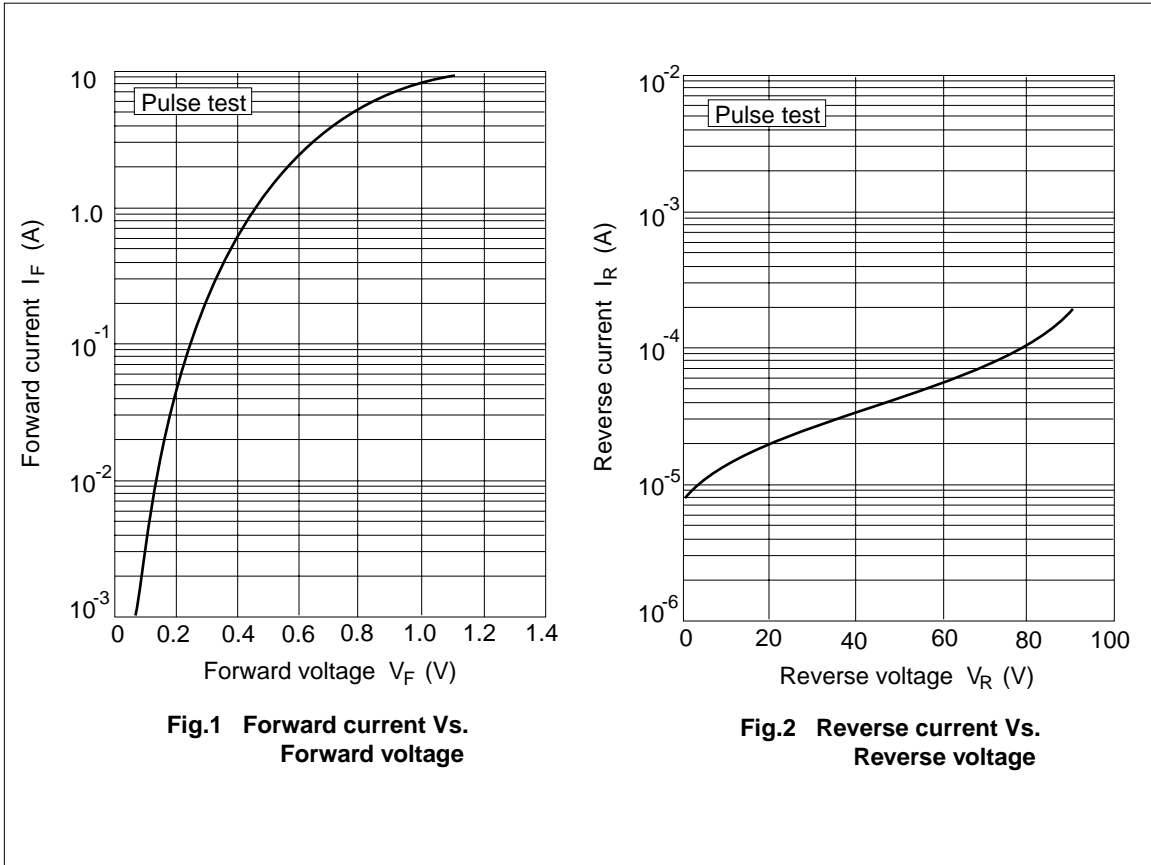
*** Half sine wave 10msec

Electrical Characteristics ($T_a = 25^\circ C$) *

| Item | Symbol | Min | Typ | Max | Unit | Test Condition |
|-----------------|----------|-----|------|------|------|----------------|
| Forward voltage | V_{F1} | — | 0.55 | 0.60 | V | $I_F = 2.0 A$ |
| | V_{F2} | — | 0.75 | 0.80 | | $I_F = 4.0 A$ |
| Reverse current | I_R | — | — | 4.0 | mA | $V_R = 90 V$ |

* Per one device

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Package Dimensions

Unit: mm

